

DATA SHEET

PEMH1; PUMH1
NPN/NPN resistor-equipped
transistors; R1 = 22 k Ω , R2 = 22 k Ω

Product specification
Supersedes data of 2001 Oct 22

2003 Oct 08

NPN/NPN resistor-equipped transistors;
R1 = 22 kΩ, R2 = 22 kΩ

PEMH1; PUMH1

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- Control of IC inputs.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	–	50	V
I _O	output current (DC)	–	100	mA
TR1	NPN	–	–	–
TR2	NPN	–	–	–
R1	bias resistor	22	–	kΩ
R2	bias resistor	22	–	kΩ

DESCRIPTION

NPN/NPN resistor-equipped transistors (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN/PNP COMPLEMENT	PNP/PNP COMPLEMENT
	PHILIPS	EIAJ			
PEMH1	SOT666		H2	PEMD2	PEMB1
PUMH1	SOT363	SC-88	H*2 ⁽¹⁾	PUMD2	PUMB1

Note

- * = p: Made in Hong Kong.
 * = t: Made in Malaysia.
 * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PEMH1 PUMH1	<p>Top view MHC650</p>	1	emitter TR1
		2	base TR1
		3	collector TR2
		4	emitter TR2
		5	base TR2
		6	collector TR1

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ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PEMH1	–	plastic surface mounted package; 6 leads	SOT666
PUMH1	–	plastic surface mounted package; 6 leads	SOT363

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	50	V
V _{CEO}	collector-emitter voltage	open base	–	50	V
V _{EBO}	emitter-base voltage	open collector	–	10	V
V _I	input voltage positive negative		–	+40	V
			–	–10	V
I _O	output current (DC)		–	100	mA
I _{CM}	peak collector current		–	100	mA
P _{tot}	total power dissipation SOT363 SOT666	T _{amb} ≤ 25 °C note 1	–	200	mW
		notes 1 and 2	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C
Per device					
P _{tot}	total power dissipation SOT363 SOT666	T _{amb} ≤ 25 °C note 1	–	300	mW
		notes 1 and 2	–	300	mW

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transistor				
$R_{th \text{ j-a}}$	thermal resistance from junction to ambient	$T_{amb} \leq 25 \text{ }^\circ\text{C}$		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
$R_{th \text{ j-a}}$	thermal resistance from junction to ambient	$T_{amb} \leq 25 \text{ }^\circ\text{C}$		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}$; $I_E = 0$	–	–	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$; $I_B = 0$	–	–	1	μA
		$V_{CE} = 30 \text{ V}$; $I_B = 0$; $T_j = 150 \text{ }^\circ\text{C}$	–	–	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}$; $I_C = 0$	–	–	180	μA
h_{FE}	DC current gain	$V_{CE} = 5 \text{ V}$; $I_C = 5 \text{ mA}$	60	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}$; $I_B = 0.5 \text{ mA}$	–	–	150	mV
$V_{i(off)}$	input-off voltage	$I_C = 100 \text{ } \mu\text{A}$; $V_{CE} = 5 \text{ V}$	–	1.1	0.8	V
$V_{i(on)}$	input-on voltage	$I_C = 5 \text{ mA}$; $V_{CE} = 0.3 \text{ V}$	2.5	1.7	–	V
R1	input resistor		15.4	22	28.6	$\text{k}\Omega$
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
C_c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$			2.5	pF

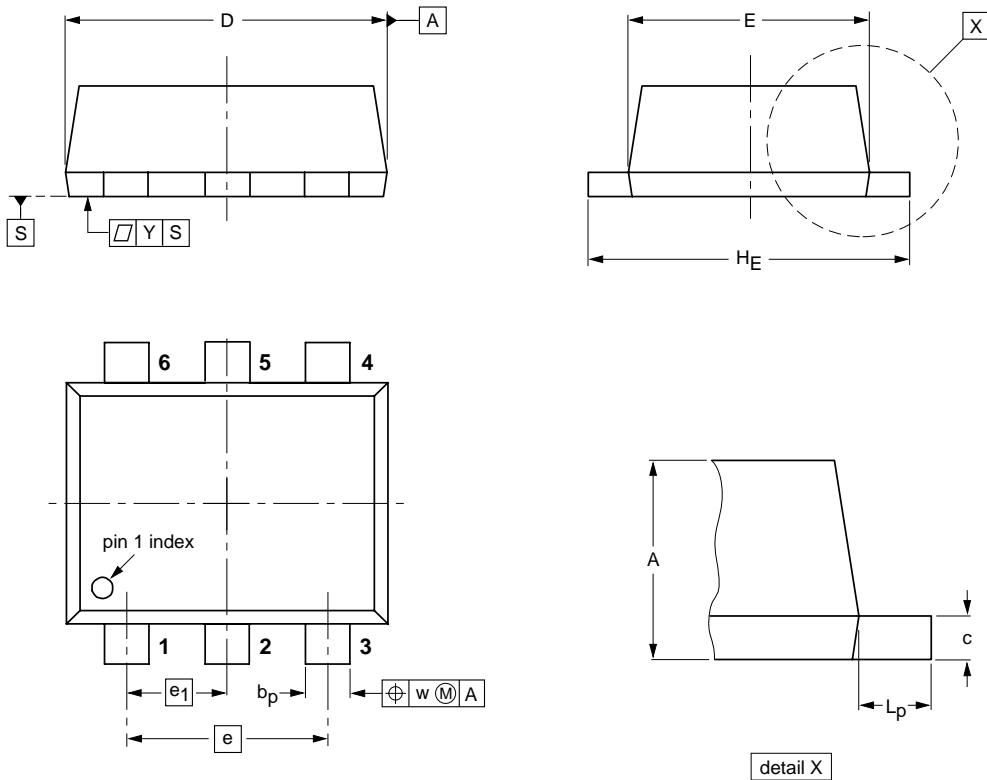
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PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	H _E	L _p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

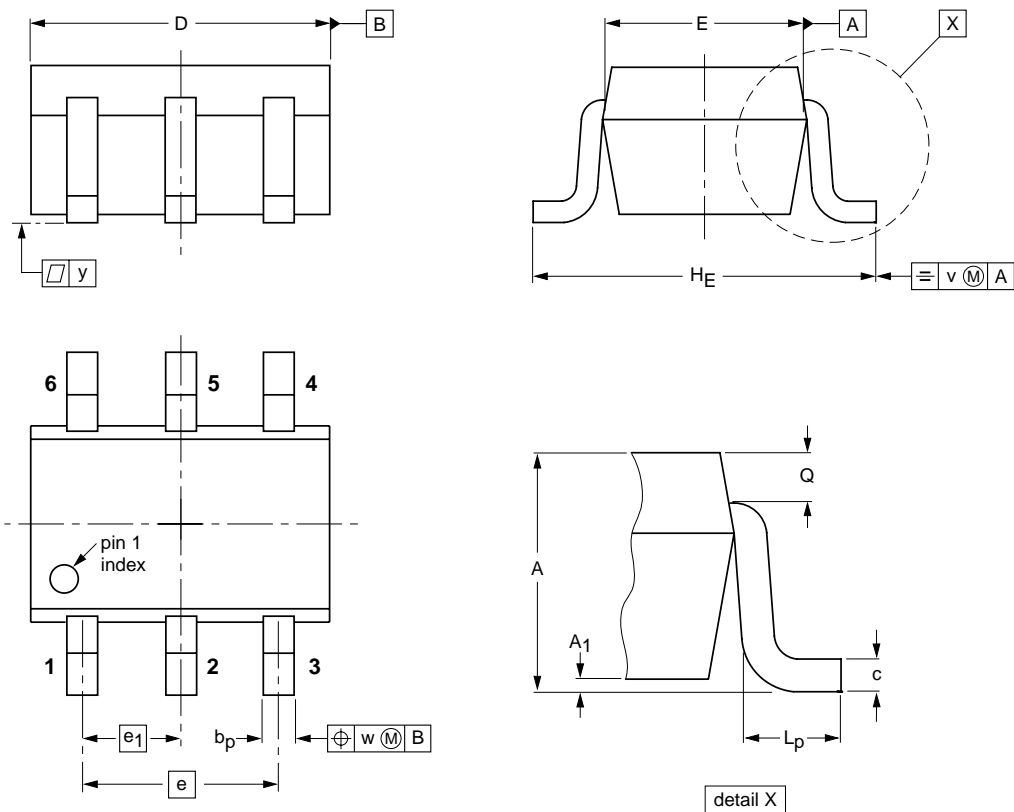
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT666					01-01-04 01-08-27

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SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max	bp	c	D	E	e	e1	HE	Lp	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT363			SC-88			97-02-28

NPN/NPN resistor-equipped transistors;
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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Printed in The Netherlands

R75/04/pp8

Date of release: 2003 Oct 08

Document order number: 9397 750 11869

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